

ABSTRACT OF THE DISCLOSURE

A light-emitting device includes an element structure including at least two semiconductor layers having mutually different conductivity types. A transparent p-side electrode of ITO is formed on the element structure. A bonding pad is formed on a region
5 of the p-side electrode. An n-side electrode made of Ti/Au is formed on the surface of the element structure opposite to the p-side electrode. A metal film made of gold plating with a thickness of about 50 μm is formed, using an Au layer in the n-side electrode as an underlying layer.